# 8-Bit Serial or Parallel-Input/ Serial-Output Shift Register

# **High-Performance Silicon-Gate CMOS**

The MC74HC165A is identical in pinout to the LS165. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device is an 8-bit shift register with complementary outputs from the last stage. Data may be loaded into the register either in parallel or in serial form. When the Serial Shift/Parallel Load input is low, the data is loaded asynchronously in parallel. When the Serial Shift/Parallel Load input is high, the data is loaded serially on the rising edge of either Clock or Clock Inhibit (see the Function Table).

The 2-input NOR clock may be used either by combining two independent clock sources or by designating one of the clock inputs to act as a clock inhibit.

#### **Features**

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 286 FETs or 71.5 Equivalent Gates
- Pb–Free Packages are Available\*



## ON Semiconductor®

http://onsemi.com

#### MARKING DIAGRAMS



PDIP-16 N SUFFIX CASE 648





SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F





SOEIAJ-16 F SUFFIX CASE 966



A = Assembly Location

L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G = Pb-Free Package
= Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

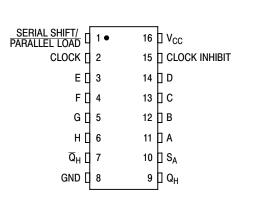


Figure 1. Pin Assignment

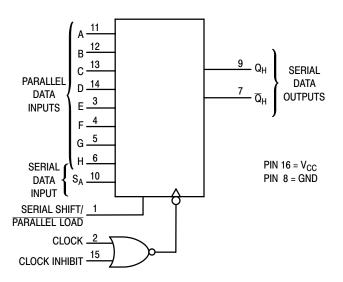


Figure 2. Logic Diagram

#### **FUNCTION TABLE**

Inputs				Interna	Stages	Output		
Serial Shift/ Parallel Load	Clock	Clock Inhibit	SA	A – H	$Q_A$	$Q_{B}$	Q <sub>H</sub>	Operation
L	Х	Х	Х	a h	а	b	h	Asynchronous Parallel Load
H H	\ \	L L	L H	X X	L H	Q <sub>An</sub> Q <sub>An</sub>	Q <sub>Gn</sub> Q <sub>Gn</sub>	Serial Shift via Clock
H H	L L	<i></i>	L H	X X	L H	Q <sub>An</sub> Q <sub>An</sub>	Q <sub>Gn</sub> Q <sub>Gn</sub>	Serial Shift via Clock Inhibit
H H	X H	H X	X X	X X		No Change		Inhibited Clock
Н	L	L	Х	Х		No Change		No Clock

X = don't care

 $Q_{An} - Q_{Gn} = Data$  shifted from the preceding stage

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HC165AN	PDIP-16	500 Units / Rail
MC74HC165ANG	PDIP-16 (Pb-Free)	500 Units / Rail
MC74HC165AD	SOIC-16	48 Units / Rail
MC74HC165ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC165ADR2	SOIC-16	2500 Units / Reel
MC74HC165ADR2G	SOIC-16 (Pb-Free)	2500 Units / Reel
MC74HC165ADTR2	TSSOP-16*	2500 Units / Reel
MC74HC165ADTR2G	TSSOP-16*	2500 Units / Reel
MC74HC165AF	SOEIAJ-16	50 Units / Rail
MC74HC165AFG	SOEIAJ-16 (Pb-Free)	50 Units / Rail
MC74HC165AFEL	SOEIAJ-16	2000 Units / Reel
MC74HC165AFELG	SOEIAJ-16 (Pb-Free)	2000 Units / Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

Specifications Brochure, BRD8011/D. \*This package is inherently Pb–Free.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
I <sub>in</sub>	DC Input Current, per Pin	± 20	mA
I <sub>out</sub>	DC Output Current, per Pin	± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 50	mA
$P_{D}$	Power Dissipation in Still Air  Plastic DIP†  SOIC Package†  TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $ \begin{array}{c} \text{V}_{\text{CC}} = 2.0 \text{ V} \\ \text{(Figure 1)} \\ \end{array}  \begin{array}{c} \text{V}_{\text{CC}} = 3.0 \text{ V} \\ \text{V}_{\text{CC}} = 4.5 \text{ V} \\ \text{V}_{\text{CC}} = 6.0 \text{ V} \end{array} $	0 0	1000 600 500 400	ns

# DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			V <sub>CC</sub>	Guaranteed Limit			
Symbol	Parameter	Test Conditions	٧	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V <sub>IL</sub>	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \ \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\begin{aligned} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} & &  I_{\text{Out}}  \leq 2.4 \text{ mA} \\ & &  I_{\text{out}}  \leq 4.0 \text{ mA} \\ & &  I_{\text{out}}  \leq 5.2 \text{ mA} \end{aligned}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	V

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			v <sub>cc</sub>	Guaranteed Limit			
Symbol	Parameter	Test Conditions	V	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \ \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{split} V_{in} = V_{IH} \text{ or } V_{IL} &   I_{out}  \leq 2.4 \text{ mA} \\ &   I_{out}  \leq 4.0 \text{ mA} \\ &   I_{out}  \leq 5.2 \text{ mA} \end{split}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μА

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_f = t_f = 6 \text{ ns}$ )

	V <sub>CC</sub>		Gua			
Symbol	Parameter	٧	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle)	2.0	6	4.8	4	MHz
max	(Figures 1 and 8)	3.0	18	17	15	
		4.5	30	24	20	
		6.0	35	28	24	
t <sub>PLH</sub> ,	Maximum Propagation Delay, Clock (or Clock Inhibit) to $Q_H$ or $\overline{Q}_H$	2.0	150	190	225	ns
$t_{PHL}$	(Figures 1 and 8)	3.0	52	63	65	
		4.5	30	38	45	
		6.0	26	33	38	
t <sub>PLH</sub> ,	Maximum Propagation Delay, Serial Shift/Parallel Load to Q <sub>H</sub> or Q <sub>H</sub>	2.0	175	220	265	ns
$t_{PHL}$	(Figures 2 and 8)	3.0	58	70	72	
		4.5	35	44	53	
		6.0	30	37	45	
t <sub>PLH</sub> ,	Maximum Propagation Delay, Input H to $Q_H$ or $\overline{Q}_H$	2.0	150	190	225	ns
t <sub>PHL</sub>	(Figures 3 and 8)	3.0	52	63	65	
		4.5	30	38	45	
		6.0	26	33	38	
t <sub>TLH</sub> ,	Maximum Output Transition Time, Any Output	2.0	75	95	110	ns
t <sub>THL</sub>	(Figures 1 and 8)	3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	16	19	
C <sub>in</sub>	Maximum Input Capacitance	-	10	10	10	pF

#### NOTES:

<sup>2.</sup> Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Package)*	40	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ . For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

<sup>1.</sup> For propagation delays with loads other than 50 pF, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# **TIMING REQUIREMENTS** (Input $t_r = t_f = 6 \text{ ns}$ )

			Guar	anteed Lim	it	
Symbol	Parameter	V <sub>CC</sub>	– 55 to 25°C	≤ <b>85</b> ° <b>C</b>	≤ 125°C	Unit
t <sub>su</sub>	Minimum Setup Time, Parallel Data Inputs to Serial Shift/Parallel Load	2.0	75	95	110	ns
	(Figure 4)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
t <sub>su</sub>	Minimum Setup Time, Input SA to Clock (or Clock Inhibit)	2.0	75	95	110	ns
	(Figure 5)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
t <sub>su</sub>	Minimum Setup Time, Serial Shift/Parallel Load to Clock (or Clock Inhibit)	2.0	75	95	110	ns
	(Figure 6)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
t <sub>su</sub>	Minimum Setup Time, Clock to Clock Inhibit	2.0	75	95	110	ns
ou	(Figure 7)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
t <sub>h</sub>	Minimum Hold Time, Serial Shift/Parallel Load to Parallel Data Inputs	2.0	5	5	5	ns
411	(Figure 4)	3.0	5	5	5	
	(1.94.0.1)	4.5	5	5	5	
		6.0	5	5	5	
t <sub>h</sub>	Minimum Hold Time, Clock (or Clock Inhibit) to Input SA	2.0	5	5	5	ns
'n	(Figure 5)	3.0	5	5	5	110
	(Figure 3)	4.5	5	5	5	
		6.0	5	5	5	
t.	Minimum Hold Time, Clock (or Clock Inhibit) to Serial Shift/Parallel Load	2.0	5	5	5	ns
t <sub>h</sub>	(Figure 6)	3.0	5	5	5	115
	(Figure 6)	3.0 4.5	5	5 5	5	
		4.5 6.0	5	5 5	5 5	
$t_{rec}$	Minimum Recovery Time, Clock to Clock Inhibit	2.0	75	95	110	ns
	(Figure 7)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
$t_{w}$	Minimum Pulse Width, Clock (or Clock Inhibit)	2.0	70	90	100	ns
	(Figure 1)	3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	16	19	
t <sub>w</sub>	Minimum Pulse width, Serial Shift/Parallel Load	2.0	70	90	100	ns
	(Figure 2)	3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	16	19	
t <sub>r</sub> , t <sub>f</sub>	Maximum Input Rise and Fall Times	2.0	1000	1000	1000	ns
11 1	(Figure 1)	3.0	800	800	800	
		4.5	500	500	500	

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### PIN DESCRIPTIONS

#### **INPUTS**

## A, B, C, D, E, F, G, H (Pins 11, 12, 13, 14, 3, 4, 5, 6)

Parallel Data inputs. Data on these inputs are asynchronously entered in parallel into the internal flip-flops when the Serial Shift/Parallel Load input is low.

#### **SA (Pin 10)**

Serial Data input. When the Serial Shift/Parallel Load input is high, data on this pin is serially entered into the first stage of the shift register with the rising edge of the Clock.

#### **CONTROL INPUTS**

#### Serial Shift/Parallel Load (Pin 1)

Data-entry control input. When a high level is applied to this pin, data at the Serial Data input (SA) are shifted into the register with the rising edge of the Clock. When a low level is applied to this pin, data at the Parallel Data inputs are asynchronously loaded into each of the eight internal stages.

## Clock, Clock Inhibit (Pins 2, 15)

Clock inputs. These two clock inputs function identically. Either may be used as an active-high clock inhibit. However, to avoid double clocking, the inhibit input should go high only while the clock input is high.

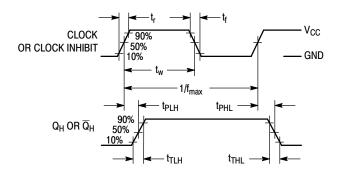
The shift register is completely static, allowing Clock rates down to DC in a continuous or intermittent mode.

#### **OUTPUTS**

### Q<sub>H</sub>, Q<sub>H</sub> (Pins 9, 7)

Complementary Shift Register outputs. These pins are the noninverted and inverted outputs of the eighth stage of the shift register.

#### **SWITCHING WAVEFORMS**



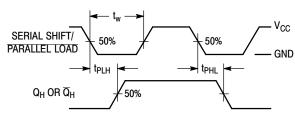


Figure 3. Serial-Shirt Mode

Figure 4. Parallel-Load Mode

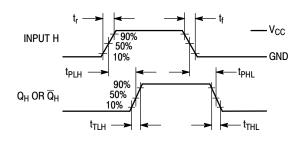


Figure 5. Parallel-Load Mode

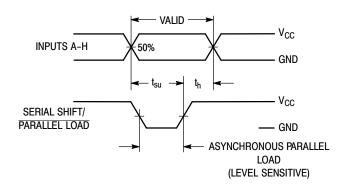


Figure 6. Parallel-Load Mode

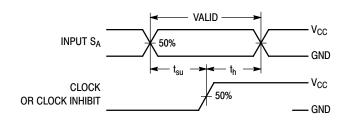


Figure 7. Serial-Shift Mode

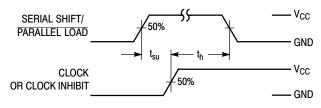


Figure 8. Serial-Shift Mode

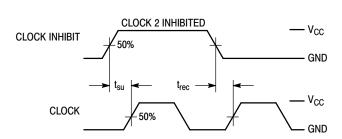
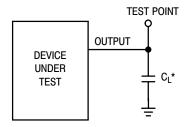


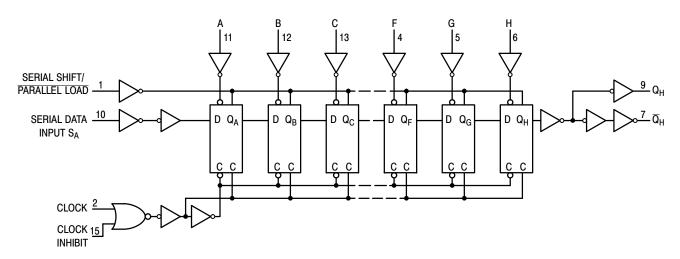
Figure 9. Serial-Shift, Clock-Inhibit Mode



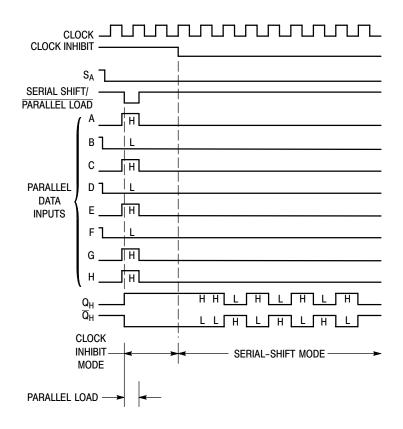
\*Includes all probe and jig capacitance

Figure 10. Test Circuit

### **EXPANDED LOGIC DIAGRAM**

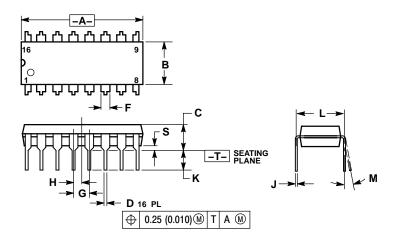


#### **TIMING DIAGRAM**



#### **PACKAGE DIMENSIONS**

#### PDIP-16 **N SUFFIX** CASE 648-08 **ISSUE T**

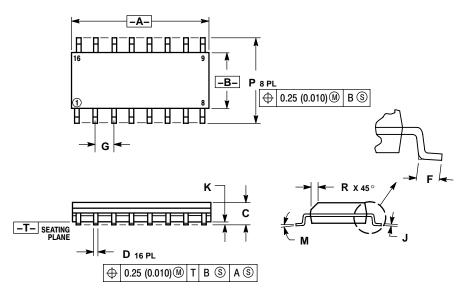


#### NOTES:

- DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLERANCING F ANSI 714.5M, 1982.
   CONTROLLING DIMENSION: INCH.
   DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
   DIMENSION B DOES NOT INCLUDE MOLD FLASH.
- 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100	BSC	2.54	BSC
Н	0.050	BSC	1.27	BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
М	0°	10 °	0°	10 °
S	0.020	0.040	0.51	1.01

#### SOIC-16 **D SUFFIX** CASE 751B-05 **ISSUE J**



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

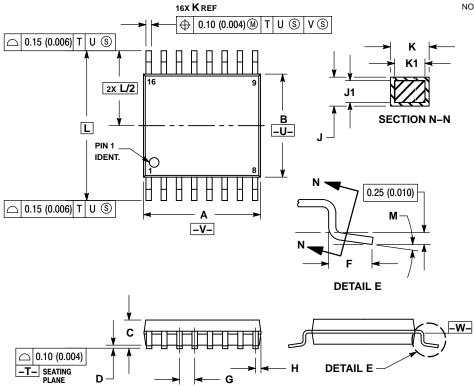
  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIGN.

- MAXIMUM MOLD PHOLICISION 0.15 (0.006)
  PER SIDE.
  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL
  IN EXCESS OF THE D DIMENSION AT
  MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050	50 BSC	
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

#### **PACKAGE DIMENSIONS**

#### TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE A**



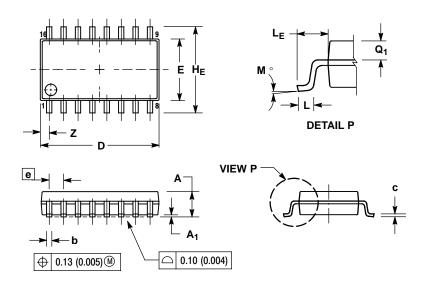
- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
    2. CONTROLLING DIMENSION: MILLIMETER.
    3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
    4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
    5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K

  - (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL
  - DIMENSION AT MAXIMUM MATERIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С	-	1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
M	0°	8°	0°	8 °	

### **PACKAGE DIMENSIONS**

SOEIAJ-16 **F SUFFIX** CASE 966-01 **ISSUE O** 



#### NOTES:

- 11ES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (6 006) PER SIDE.
- OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q	0.70	0.90	0.028	0.035
Z		0.78		0.031

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